

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently Amended) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure wherein said discontinuous film is a stressed film.

2. (Previously Presented) A field effect transistor as recited in claim 1, wherein said discontinuity is self-aligned to said gate structure.

3. (Canceled)

4. (Currently Amended) A field effect transistor as recited in claim 3 1, wherein said stressed film comprises an insulator.

5. (Canceled)